**IN THE CLAIMS**

Claims 1-13 (Withdrawn).

14. (Currently Amended) A method of manufacturing a semiconductor [apparatus] device comprising the steps of:

forming a bypass film from an insulation film through which a leak current is able to [easily] flow [as compared with a gate insulation film of a MIS transistor];

forming a gate electrode for controlling [said] a MIS transistor which extends above said bypass film and is electrically coupled to said bypass film; and

performing a [work] process [directed to the manufacture of] on the semiconductor [apparatus while performing destaticization through said bypass film] device during the manufacturing of the device that forms a current in the gate electrode, wherein the current is leaked from the gate electrode to the bypass film.

15. (Currently Amended) A method of manufacturing a semiconductor [apparatus] device according to claim 14, further comprising the steps of:

selectively etching a gate insulation film of a region forming said bypass film to make the same thin after said gate insulation film of said MIS transistor has been formed; and

forming said gate electrode to have a pattern extending from a region of said MIS transistor to a portion above said bypass film; and

performing a process on the semiconductor device during the manufacturing of the device that forms a current in the gate electrode, wherein the current is leaked from the gate electrode to the bypass film.

16. (Currently Amended) A method of manufacturing a semiconductor [apparatus] device according to claim 14, further comprising the steps of:

forming a first gate insulation film of said MIS transistor, then selectively etching off said first gate insulation film at a region of said bypass film and forming a second gate insulation film which will become said bypass film; and

then forming said gate electrode to have a pattern extending from a region of said MIS transistor to a portion above said bypass film; and

performing a process on the semiconductor device during the manufacturing of the device that forms a current in the device, wherein the current is leaked to the bypass film.

17. (Currently Amended) A method of manufacturing a solid state image device comprising the steps of:

forming a bypass film through which a leak current is able to easily flow as compared with a gate insulation film, between a wiring for connecting each gate [electrodes] electrode of a MOS transistor forming the pixel; [and a drain region located other than within any active region; and]

carrying out a work process while performing destaticization through said bypass film; and

performing a process on the semiconductor device during the manufacturing of the device that forms a current in a gate electrode, wherein the current is leaked from the gate electrode to the bypass film.